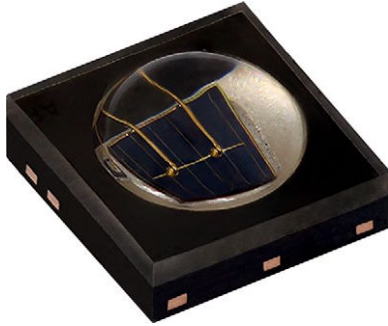


# High Power Infrared Emitting Diode, 850 nm, Surface Emitter Technology



## FEATURES

- Package type: surface-mount
- Package form: high power SMD with lens
- Dimensions (L x W x H in mm): 3.4 x 3.4 x 1.8
- Peak wavelength:  $\lambda_p = 850 \text{ nm}$
- AEC-Q102 qualified
- Angle of half intensity:  $\phi = \pm 60^\circ$
- Designed for high drive currents: up to 1.5 A (DC) and up to 5 A (pulsed)
- Low thermal resistance:  $5 \text{ K/W} < R_{thJP} < 9 \text{ K/W}$
- ESD: up to 5 kV (according to ANSI / ESDA / JEDEC® JS-001)
- Floor life: 168 h, MSL 3, according to J-STD-020E
- Lead (Pb)-free reflow soldering
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

AUTOMOTIVE  
GRADE

**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
**GREEN**  
(5-2008)

## LINKS TO ADDITIONAL RESOURCES



## DESCRIPTION

As part of the [Astral](#) portfolio, the VSMA1085600X02 is an infrared, 850 nm emitting diode. It features a double stack emitter chip for highest radiant power. The 42 mil chip size allows 1.5 A DC operation and supports pulsed currents up to 5.0 A.

## APPLICATIONS

- Driver and occupant monitoring
- Eye tracking
- Safety and security, CCTV

## PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr) at $I_F = 1.0 \text{ A}$	$\phi$ (°)	$\lambda_p$ (nm)	$\lambda_{\text{centroid}}$ (nm)	$t_r$ (ns)
VSMA1085600X02	510	$\pm 60$	850	845	13

### Note

- Test conditions see table “Basic Characteristics”

## ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSMA1085600X02	Tape and reel	MOQ: 600 pcs, 600 pcs/reel	High power with lens

### Note

- MOQ: minimum order quantity



ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Minimum forward current		$I_{F, min.}$	100	mA
Forward current		$I_F$	1.5	A
Surge forward current	$t_p = 100\text{ }\mu\text{s}$	$I_{FSM}$	5	A
Power dissipation		$P_V$	5.33	W
Junction temperature		$T_J$	145	$^{\circ}\text{C}$
Ambient temperature range		$T_{amb}$	-40 to +125	$^{\circ}\text{C}$
Storage temperature range		$T_{stg}$	-40 to +125	$^{\circ}\text{C}$
Soldering temperature	According to Fig. 11, J-STD-020E	$T_{sd}$	260	$^{\circ}\text{C}$
Thermal resistance junction to solder point real <sup>(1)</sup>	JESD 51	$R_{thJSP, real}$	5 to 9	K/W
Thermal resistance junction to ambient real	JESD 51	$R_{thJA, real}$	80	K/W
ESD sensitivity	According to ANSI / ESDA / JEDEC JS-001	$V_{ESD}$	5	kV

**Note**

- <sup>(1)</sup> Thermal resistance junction to solder point real has been measured with the part mounted on an ideal heatsink and the optical output power has been deducted from the total electrical power dissipation

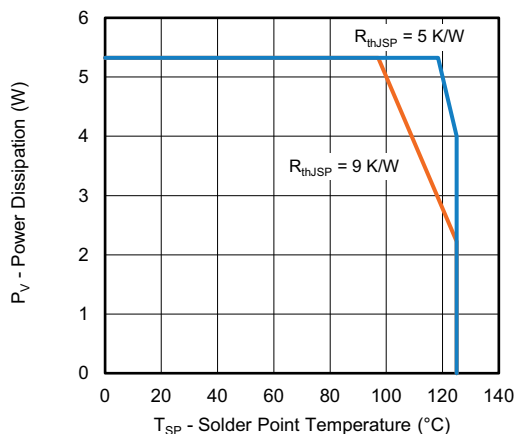


Fig. 1 - Power Dissipation Limit vs. Solder Point Temperature

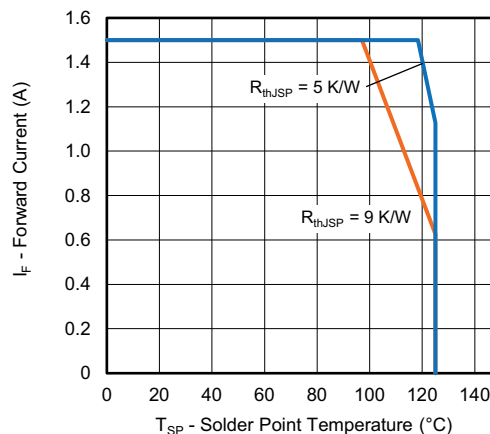


Fig. 2 - Forward Current Limit vs. Solder Point Temperature

<b>BASIC CHARACTERISTICS</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 0.35\text{ A}$ , $t_p = 10\text{ ms}$	$V_F$	2.7	2.8	3.1	V
	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$V_F$	2.8	3.0	3.3	V
	$I_F = 1.5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$V_F$	2.9	3.2	3.55	V
	$I_F = 5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$V_F$	3.2	3.9	4.4	V
Temperature coefficient of $V_F$	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$		-	-2	-	mV/K
Reverse current <sup>(1)</sup>		$I_R$	Not designed for reverse operation			$\mu\text{A}$
Radiant intensity <sup>(2)</sup>	$I_F = 0.35\text{ A}$ , $t_p = 10\text{ ms}$	$I_e$	130	190	235	mW/sr
	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$I_e$	360	510	630	mW/sr
	$I_F = 1.5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$I_e$	535	750	950	mW/sr
	$I_F = 5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$I_e$	1620	2300	2850	mW/sr
Radiant power	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$\phi_e$	-	1450	-	mW
	$I_F = 1.5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$\phi_e$	-	2125	-	mW
Temperature coefficient of $\phi$	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$TK_{\phi}$	-	-0.15	-	%/K
Angle of half intensity		$\phi$	-	$\pm 60$	-	$^{\circ}$
Peak wavelength	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$\lambda_p$	-	850	-	nm
Centroid wavelength	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$\lambda_{\text{centroid}}$	-	845	-	nm
Spectral bandwidth	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$\Delta\lambda$	-	30	-	nm
Temperature coefficient of $\lambda_p$	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$TK_{\lambda_p}$	-	0.25	-	nm/K
Rise time	$I_F = 1\text{ A}$ , $R_L = 50\text{ }\Omega$	$t_r$	-	13	-	ns
Fall time	$I_F = 1\text{ A}$ , $R_L = 50\text{ }\Omega$	$t_f$	-	16	-	ns

**Notes**

- (1) This infrared LED is designed to be operated within the specified forward current range. Continuous reverse operation must be avoided because it may damage the infrared LED.
- (2) The radiant intensity values have been measured with a tolerance of  $\pm 11\%$

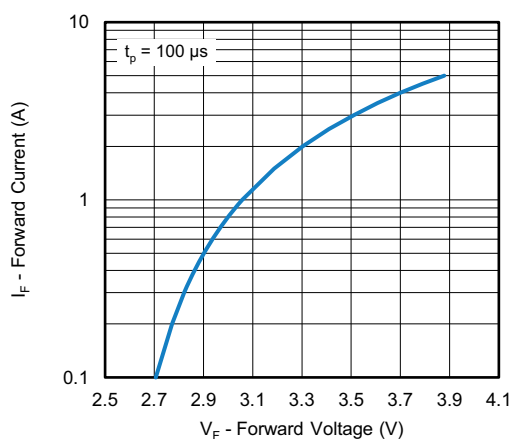
**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)


Fig. 3 - Forward Current vs. Forward Voltage

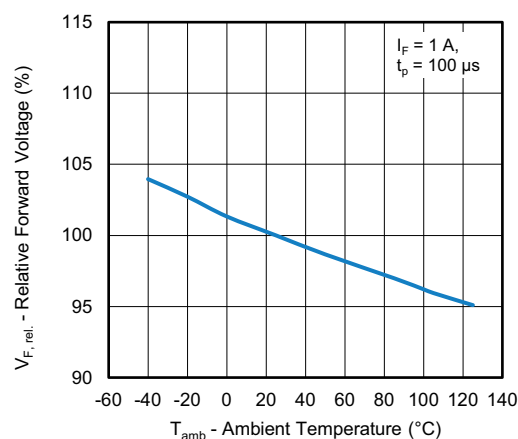


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

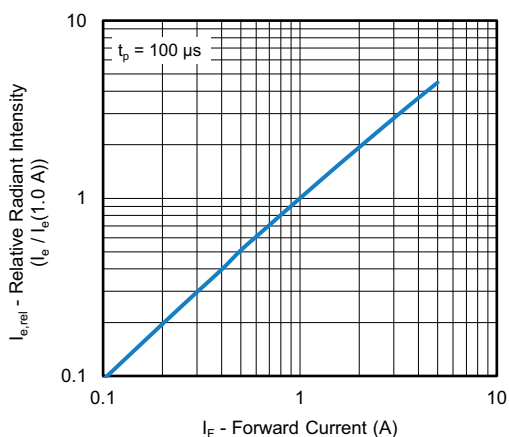


Fig. 5 - Relative Radiant Intensity vs. Forward Current

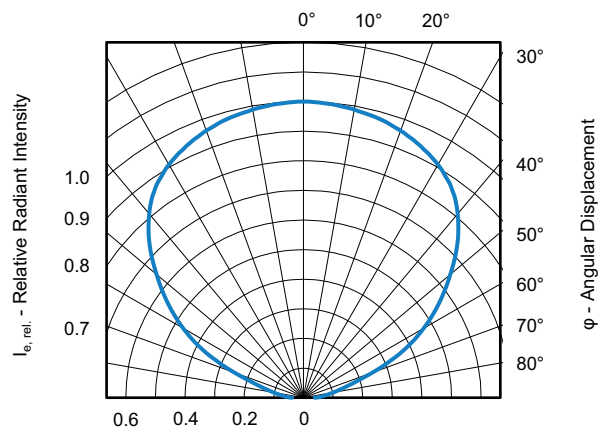


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

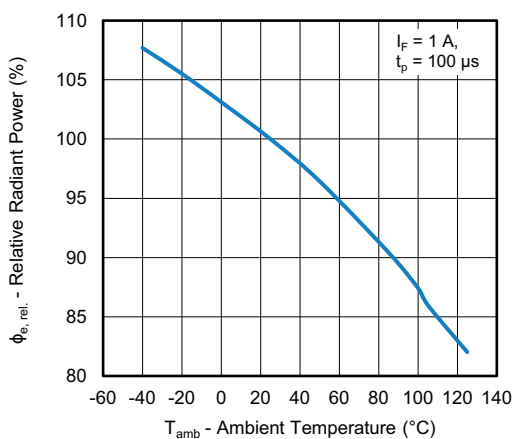


Fig. 6 - Relative Radiant Power vs. Ambient Temperature

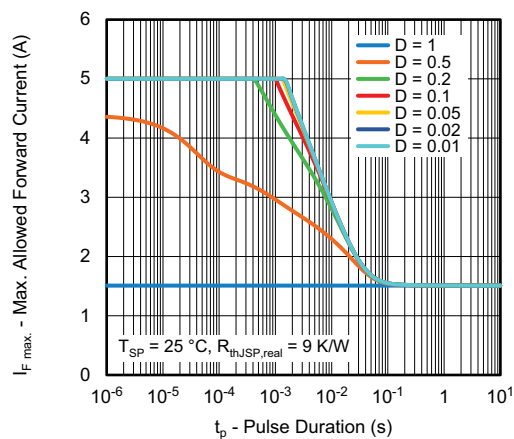


Fig. 9 - Max. Allowed Forward Current vs. Pulse Duration

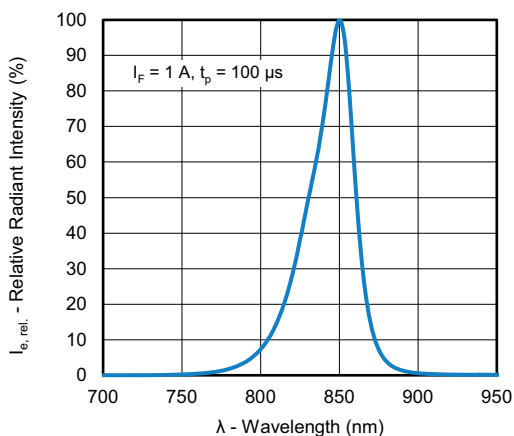


Fig. 7 - Relative Radiant Intensity vs. Wavelength

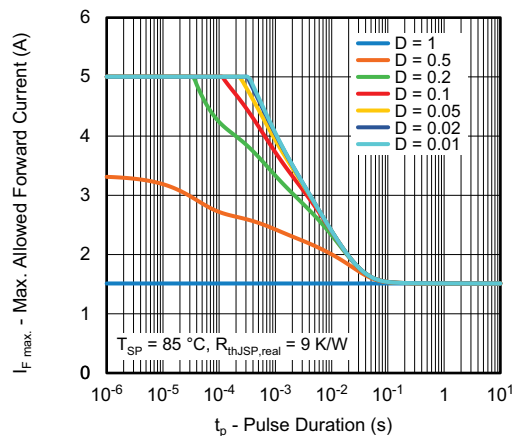
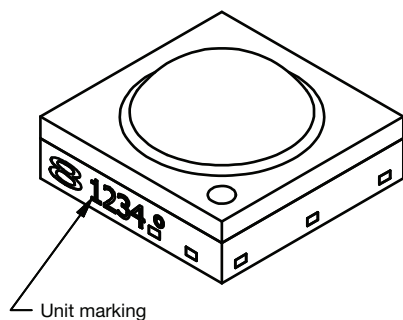
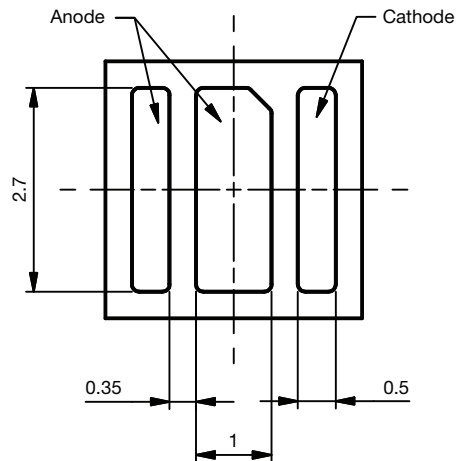
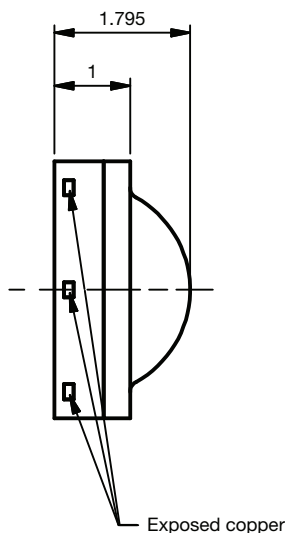
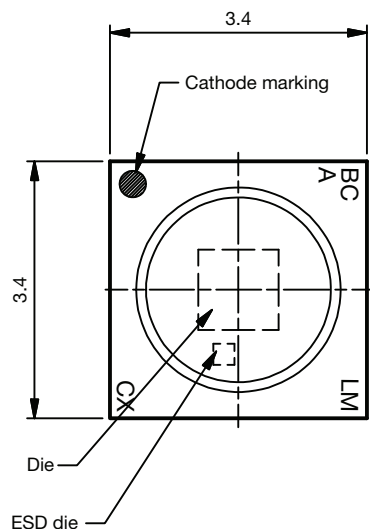


Fig. 10 - Max. Allowed Forward Current vs. Pulse Duration

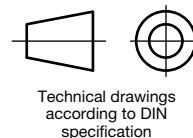




**PACKAGE DIMENSIONS** in millimeters



Not indicated tolerances  $\pm 0.1$

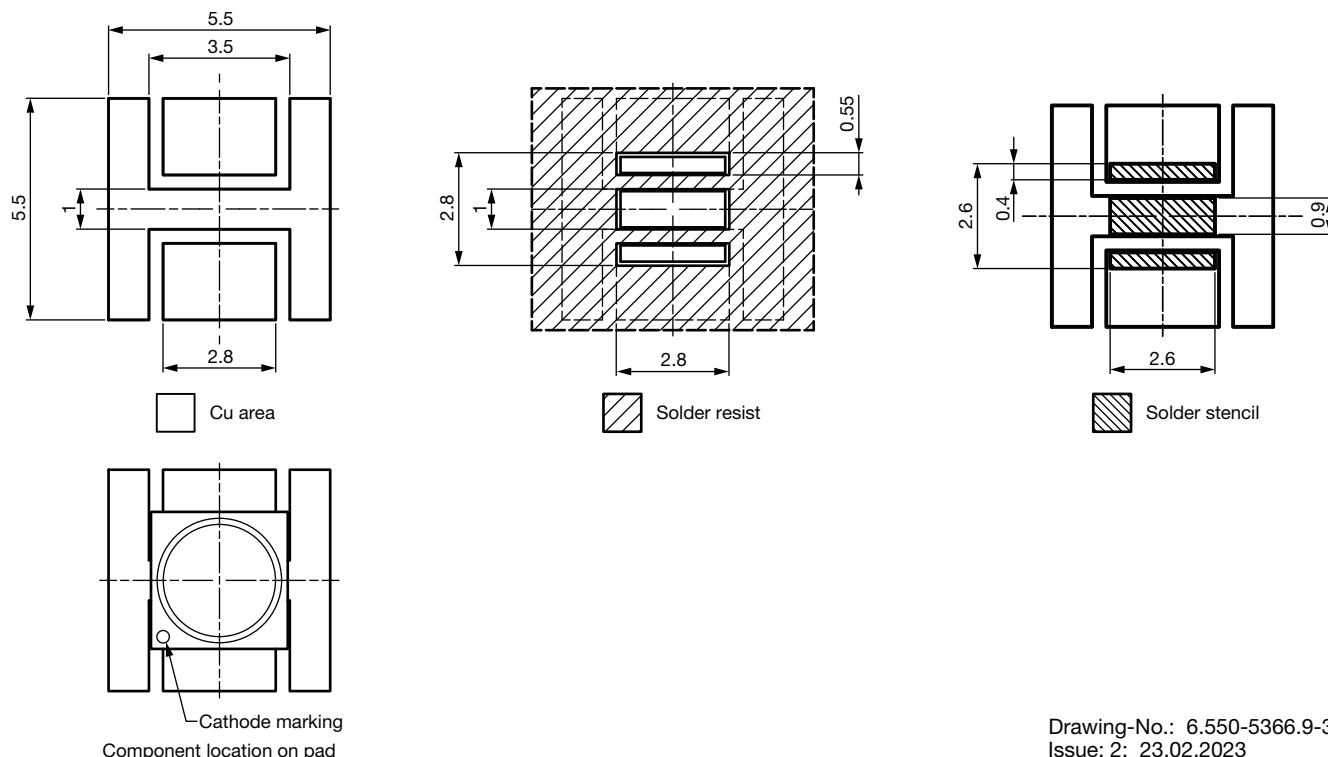


Drawing-No.: 6.550-5368.01-4  
Issue: 2; 22.03.2023

**Notes**

- Tolerance is  $\pm 0.10$  mm (0.004") unless otherwise noted
- Specifications are subject to change without notice

## RECOMMENDED FOOTPRINT



## SOLDER PROFILE

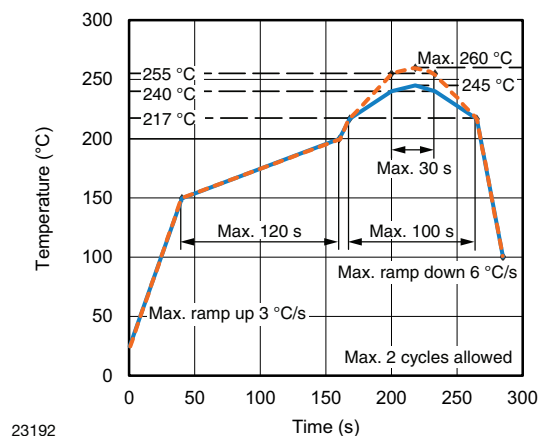


Fig. 11 - Lead (Pb)-free (Sn) Infrared Reflow Solder Profile According to J-STD-020E for Surface-Mount Components

## DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

## FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 168 h

Conditions:  $T_{amb} < 30\text{ °C}$ ,  $RH < 60\%$

Moisture sensitivity level 3, according to J-STD-020E

## DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-033D or label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C),  $RH < 5\%$ .



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